Integrated Device Technology, Inc.

CMOS STATIC RAMS 64K (16K x 4-BIT)

IDT 7198S
IDT 7198L

Added Chip Select and Output Enable Controls

T-46-23-10

FEATURES:

- Optimized for fast RISC processors, including IDT79R3000
- Fast Output Enable ($\overline{OE}$) pin available for added system flexibility
- Multiple Chip Selects ($\overline{CS_1}$, $\overline{CS_2}$) simplify system design and operation
- High speed (equal access and cycle times)
  - Military: 20/25/30/35/45/55/70/85ns (max.)
  - Commercial: 15/19/20/25/30/35/45ns (max.)
- Low power consumption
  - IDT7198S
    - Active: 350mW (typ.)
    - Standby: 100µw (typ.)
  - IDT7198L
    - Active: 300mW (typ.)
    - Standby: 30µw (typ.)
- Battery back-up operation—2V data retention (L version only)
- 24-pin THINDIP, 24-pin plastic DIP, high-density 28-pin leadless chip carrier, 24-pin SOIC, flatpack and CERPACK
- Produced with advanced CEMOS™ technology
- Bidirectional data inputs and outputs
- Inputs/outputs TTL-compatible
- Three-state outputs
- Military product compliant to MIL-STD-883, Class B
- Standard Military Drawing# 5962-86859 is pending listing on this function. Refer to Section 2/page 2-4.

DESCRIPTION:

The IDT7198 is a 65,536 bit high-speed static RAM organized as 16K x 4. It is fabricated using IDT's high-performance, high-reliability technology—CEMOS. This state-of-the-art technology, combined with innovative circuit design techniques, provides a cost effective approach for memory intensive applications. Timing parameters have been specified to meet the speed demands of the fastest IDT79R3000 RISC processors.

The IDT7198 features three memory control functions: Chip Select 1 ($\overline{CS_1}$), Chip Select 2 ($\overline{CS_2}$) and Output Enable ($\overline{OE}$). These three functions greatly enhance the IDT7198's overall flexibility in high-speed memory applications.

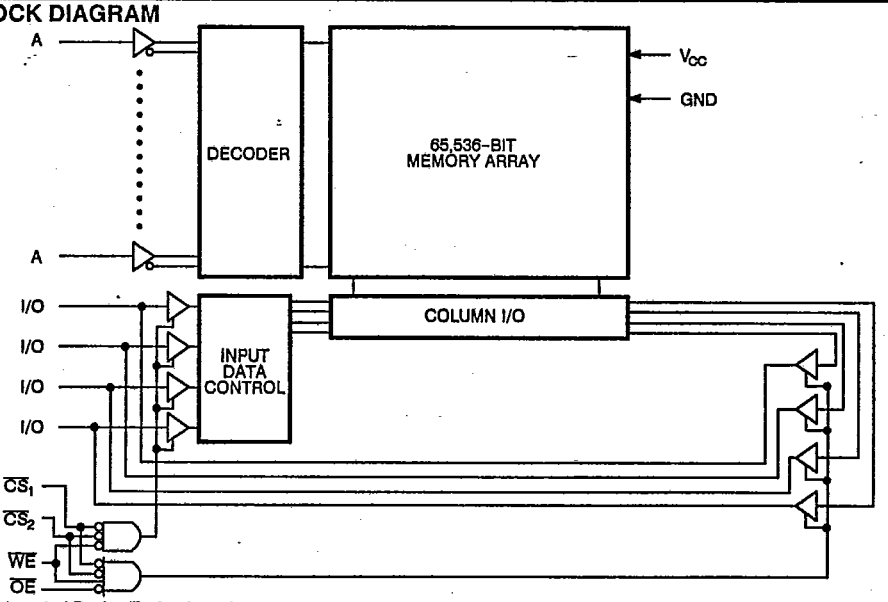
Access times as fast as 15ns are available, with typical power consumption of only 300mW. The IDT7198 offers a reduced power standby mode, I_{SB1}, which enables the designer to considerably reduce device power requirements. This capability significantly decreases system power and cooling levels, while greatly enhancing system reliability. The low-power version (L) also offers a battery backup data retention capability where the circuit typically consumes only 30µW when operating from a 2V battery.

All inputs and outputs are TTL-compatible and operate from a single 5 volt supply. Fully static asynchronous circuitry, along with matching access and cycle times, favor the simplified system design approach.

The IDT7198 is packaged in either a 24-pin ceramic DIP, 24-pin plastic DIP, 28-pin leadless chip carrier, 24-pin SOIC and 24-pin flatpack or CERPACK, providing improved board-level packing densities.

Military grade product is manufactured in compliance with the latest revision of MIL-STD-883, Class B, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

FUNCTIONAL BLOCK DIAGRAM



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MEMORY CONTROL:

The IDT7198 64K high-speed CEMOS static RAM incorporates two additional memory control features (an extra chip select and an output enable pin) which offer additional benefits in many system memory applications.

The dual chip select feature ($\overline{CS_1}$, $\overline{CS_2}$) now brings the convenience of improved system speeds to the large memory designer by reducing the external logic required to perform decoding. Since external decoding logic is reduced, board space is saved, system speed is enhanced by approximately 10-20ns and system reliability improves as a result of lower parts count. (See technical note 1 "Using Two Chip Selects on the IDT7198.")

Both chip selects, Chip Select 1($\overline{CS_1}$) and Chip Select 2 ($\overline{CS_2}$), must be in the active-low state to select the memory. If either chip select is pulled high, the memory will be deselected and remain in the standby mode.

The fast output enable function ($\overline{OE}$) is also a highly desirable feature of the IDT7198 high-speed common I/O static RAM. This function is designed to eliminate problems associated with data bus contention by allowing the data outputs to be controlled independent of either chip select. Its speed permits further decreases in overall read cycle timing.

These added memory control features provide improved system design flexibility, along with overall system speed performance enhancements.

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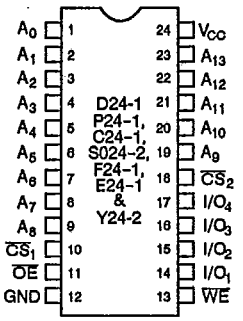
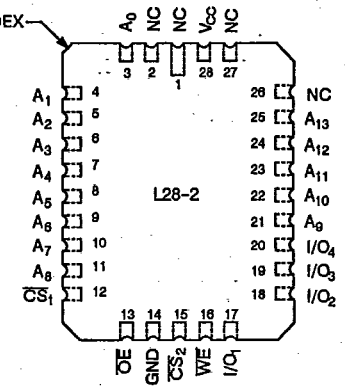
PIN CONFIGURATION

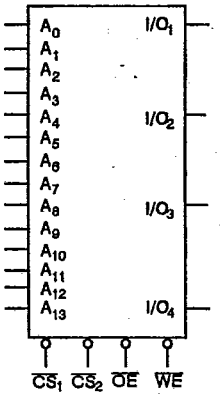


DIP/SOIC/FLATPACK/CERPACK
TOP VIEW



LCC
TOP VIEW

LOGIC SYMBOL



PIN NAMES

A_0–A_{13}	Address Inputs	$\overline{OE}$	Output Enable
$\overline{CS_1}$	Chip Select 1	I/O_1 -I/O_4	Data I/O
$\overline{CS_2}$	Chip Select 2	V_{CC}	Power
$\overline{WE}$	Write Enable	GND	Ground

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ABSOLUTE MAXIMUM RATINGS (1)

SYMBOL	RATING	COMMERCIAL	MILITARY	UNIT
V_{TERM}	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
T_A	Operating Temperature	0 to +70	-55 to +125	°C
T_{BIAS}	Temperature Under Bias	-55 to +125	-65 to +135	°C
T_{STG}	Storage Temperature	-55 to +125	-65 to +150	°C
P_T	Power Dissipation	1.0	1.0	W
I_{OUT}	DC Output Current	50	50	mA

NOTE:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
V_{CC}	Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
V_{IH}	Input High Voltage	2.2	–	6.0	V
V_{IL}	Input Low Voltage	-0.5(1)	–	0.8	V

NOTE:

1. V_{IL} (min.) = -3.0V for pulse width less than 20ns.

RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

GRADE	AMBIENT TEMPERATURE	GND	V_{CC}
Military	-55°C to +125°C	0V	5.0V ± 10%
Commercial	0°C to +70°C	0V	5.0V ± 10%

DC ELECTRICAL CHARACTERISTICS

V_{CC} = 5.0V ±10%

SYMBOL	PARAMETER	TEST CONDITION		IDT7198S MIN.	IDT7198S TYP.(1)	IDT7198S MAX.	IDT7198L MIN.	IDT7198L TYP.(1)	IDT7198L MAX.	UNIT
$\|I_{LI}\|$	Input Leakage Current	V_{CC} = Max., V_{IN} = GND to V_{CC}	MIL.	–	–	10	–	–	5	µA
			COM'L.	–	–	5	–	–	2	
$\|I_{LO}\|$	Output Leakage Current	V_{CC} = Max. $\overline{CS}$ = V_{IH}, V_{OUT} = GND to V_{CC}	MIL.	–	–	10	–	–	5	µA
			COM'L.	–	–	5	–	–	2	
V_{OL}	Output Low Voltage	I_{OL} = 10mA, V_{CC} = Min.		–	–	0.5	–	–	0.5	V
		I_{OL} = 8mA, V_{CC} = Min.		–	–	0.4	–	–	0.4	V
V_{OH}	Output High Voltage	I_{OH} = -4mA, V_{CC} = Min.		2.4	–	–	2.4	–	–	V

NOTE:

1. Typical limits are at V_{CC} = 5.0V, +25°C ambient.

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DC ELECTRICAL CHARACTERISTICS[1]

V_{CC} = 5.0V ±10%, V_{LC} = 0.2V, V_{HC} = V_{CC} – 0.2V

SYMBOL	PARAMETER	POWER	7198S15		7198S19/20		7198S25 7198L25		7198S30/35 7198L30/35		7198S45/55[3] 7198L45/55[3]		7198S70[3] 7198L70[3]		7198S85[3] 7198L85[3]		UNIT
			COM'L.	MIL.	COM'L.	MIL.	COM'L.	MIL.	COM'L.	MIL.	COM'L.	MIL.	COM'L.	MIL.	COM'L.	MIL.	
I_{CC1}	Operating Power Supply Current $\overline{CS}$ = V_{IL}, Outputs Open V_{CC} = Max., f = 0[2]	S	135	–	120	140	100	125	100	110	100	110	–	110	–	110	mA
		L	–	–	–	–	85	110	85	95	85	95	–	95	–	95	
I_{CC2}	Dynamic Operating Current $\overline{CS}$ = V_{IL}, Outputs Open, V_{CC} = Max., f = f_{MAX}[2]	S	180	–	155	175	135	155	125	140	125	140	–	140	–	140	mA
		L	–	–	–	–	125	145	115/105	125/115	100	110	–	110	–	105	
I_{SB}	Standby Power Supply Current (TTL Level) $\overline{CS}$ ≥ V_{IH}, V_{CC} = Max., Outputs Open f = f_{MAX}[2]	S	75	–	60	70	55	60	50/45	55/50	45	50	–	50	–	50	mA
		L	–	–	–	–	45	50	40/35	45/40	30	35	–	35	–	35	
I_{SB1}	Full Standby Power Supply Current (CMOS Level) $\overline{CS}$ ≥ V_{HC}, V_{CC} = Max., V_{IN} ≥ V_{HC} or V_{IN} ≤ V_{LC}, f = 0[2]	S	25	–	20	25	15	20	15	20	15	20	–	20	–	20	mA
		L	–	–	–	–	0.5	1.5	0.5	1.5	0.5	1.5	–	1.5	–	1.5	

NOTES:

1. All values are maximum guaranteed values.
2. At f = f_{MAX} address and data inputs are cycling at the maximum frequency of read cycles of $1/t_{RC}$. f = 0 means no input lines change.
3. –55°C to +125°C temperature range only.

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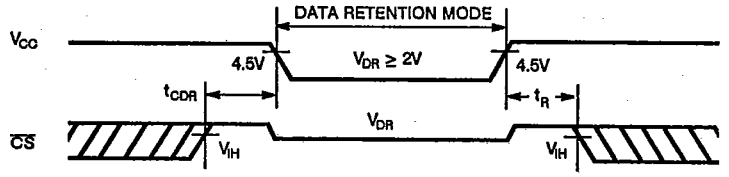
DATA RETENTION CHARACTERISTICS OVER ALL TEMPERATURE RANGES

(L Version Only) V_{LC} = 0.2V, V_{HC} = V_{CC} – 0.2V

SYMBOL	PARAMETER	TEST CONDITION		MIN.	TYP.(1) V_{CC} @ 2.0V	TYP.(1) V_{CC} @ 3.0V	MAX. V_{CC} @ 2.0V	MAX. V_{CC} @ 3.0V	UNIT
V_{DR}	V_{CC} for Data Retention	–		2.0	–	–	–	–	V
I_{CCDR}	Data Retention Current	$\overline{CS} \geq V_{HC}$ $V_{IN} \geq V_{HC}$ or $\leq V_{LC}$	MIL.	–	10	15	600	900	µA
			COM'L.	–	10	15	150	225	
t_{CDR}(3)	Chip Deselect to Data Retention Time			0	–		–		ns
t_R(3)	Operation Recovery Time			t_{RC}(2)	–		–		ns
$\|I_{LI}\|$(3)	Input Leakage Current			–	–		2		µA

NOTES:
1. T_A = +25°C
2. t_{RC} = Read Cycle Time
3. This parameter is guaranteed but not tested.

LOW V_{CC} DATA RETENTION WAVEFORM



AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	See Figures 1 and 2

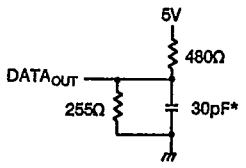


Figure 1. Output Load

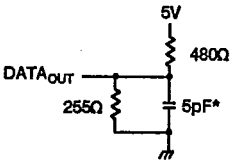


Figure 2. Output Load (for $t_{CLZ1, 2}$, t_{OLZ}, $t_{CHZ1, 2}$, t_{OHZ}, t_{OW} and t_{WHZ})

* Including scope and jig.

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AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5V ±10%, All Temperature Ranges)

SYMBOL	PARAMETER	7198S15[1]19/20[5] MIN.	MAX.	7198S25/30 7198L25/30 MIN.	MAX.	7198S35/45 7198L35/45 MIN.	MAX.	7198S55[2] 7198L55[2] MIN.	MAX.	7198S70[2] 7198L70[2] MIN.	MAX.	7198S85[2] 7198L85[2] MIN.	MAX.	UNIT
READ CYCLE														
t_{RC}	Read Cycle Time	15/20/20	–	25/30	–	35/45	–	55	–	70	–	85	–	ns
t_{AA}	Address Access Time	–	15/19/20	–	25/29	–	35/45	–	55	–	70	–	85	ns
$t_{ACS1,2}$	Chip Select-1, 2 Access Time[3]	–	15/20/20	–	25/30	–	35/45	–	55	–	70	–	85	ns
$t_{CLZ1,2}$	Chip Select-1, 2 to Output in Low Z[4]	5	–	5	–	5	–	5	–	5	–	5	–	ns
t_{OE}	Output Enable to Output Valid	–	8/9/9	–	11/18	–	20/25	–	35	–	45	–	55	ns
t_{OLZ}	Output Enable to Output in Low Z[4]	5	–	5	–	5	–	5	–	5	–	5	–	ns
$t_{CHZ1,2}$	Chip Select-1, 2 to Output in High Z[4]	–	7/8/8	–	10/12	–	14	–	20	–	25	–	30	ns
t_{OHZ}	Output Disable to Output in High Z[4]	–	7/8/8	–	9/12	–	15	–	20	–	25	–	30	ns
t_{OH}	Output Hold from Address Change	5	–	5	–	5	–	5	–	5	–	5	–	ns
t_{PU}	Chip Select to Power Up Time[4]	0	–	0	–	0	–	0	–	0	–	0	–	ns
t_{PD}	Chip Deselect to Power Down Time[4]	–	15/20/20	–	25/30	–	35/45	–	55	–	70	–	85	ns

NOTES:
1. 0°C to +70°C temperature range only.
2. –55°C to +125°C temperature range only.
3. Both chip selects must be active low for the device to be selected.
4. This parameter guaranteed but not tested.
5. Preliminary data only for military devices.

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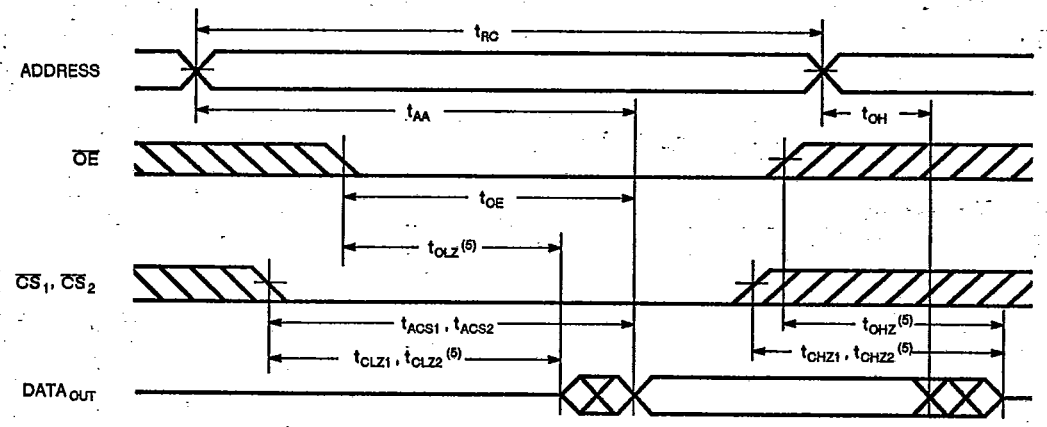
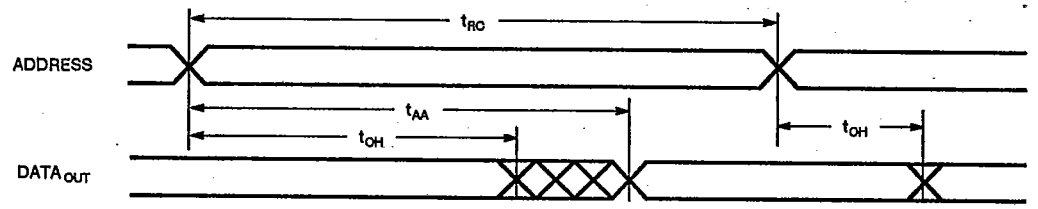
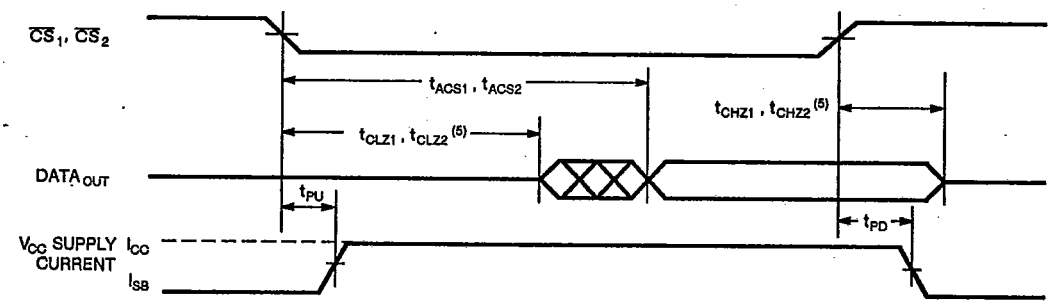
TIMING WAVEFORM OF READ CYCLE NO. 1 (1)



TIMING WAVEFORM OF READ CYCLE NO. 2 (1, 2, 4)



TIMING WAVEFORM OF READ CYCLE NO. 3 (1, 3, 4)



NOTES:
1. $\overline{WE}$ is High for Read Cycle.
2. Device is continuously selected, $\overline{CS_1} = V_{IL}$, $\overline{CS_2} = V_{IL}$.
3. Address valid prior to or coincident with $\overline{CS_1}$ and or $\overline{CS_2}$ transition low.
4. $\overline{OE} = V_{IL}$
5. Transition is measured ±200mV from steady state.

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AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5V ±10%, All Temperature Ranges)

SYMBOL	PARAMETER	7198S15[1]19/20[5] MIN.	MAX.	7198S25/30 7198L25/30 MIN.	MAX.	7198S35/45 7198L35/45 MIN.	MAX.	7198S55[2] 7198L55[2] MIN.	MAX.	7198S70[2] 7198L70[2] MIN.	MAX.	7198S85[2] 7198L85[2] MIN.	MAX.	UNIT
WRITE CYCLE														
t_{WC}	Write Cycle Time	13/17/17	–	20/22	–	30/40	–	50	–	60	–	75	–	ns
$t_{CW1,2}$	Chip Select to End of Write[3]	13/17/17	–	20/22	–	25/35	–	50	–	60	–	75	–	ns
t_{AW}	Address Valid to End of Write	13/17/17	–	20/22	–	25/35	–	50	–	60	–	75	–	ns
t_{AS}	Address Set-up Time	0	–	0	–	0	–	0	–	0	–	0	–	ns
t_{WP}	Write Pulse Width	13/17/17	–	20/22	–	25/35	–	50	–	60	–	75	–	ns
$t_{WR1,2}$	Write Recovery Time	0	–	0	–	0	–	0	–	0	–	0	–	ns
t_{WHZ}	Write Enable to Output High Z[4]	–	5/6/6	–	7/10	–	10/15	–	25	–	30	–	40	ns
t_{DW}	Data Valid to End of Write	8/10/10	–	13	–	15/20	–	25	–	30	–	35	–	ns
t_{DH}	Data Hold Time	0	–	0	–	0	–	0	–	0	–	0	–	ns
t_{OW}	Output Active from End of Write[4]	5	–	5	–	5	–	5	–	5	–	5	–	ns

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NOTES:
1. 0°C to +70°C temperature range only.
2. -55°C to +125°C temperature range only.
3. Both chip selects must be active low for the device to be selected.
4. This parameter guaranteed but not tested.
5. Preliminary data only for military devices.

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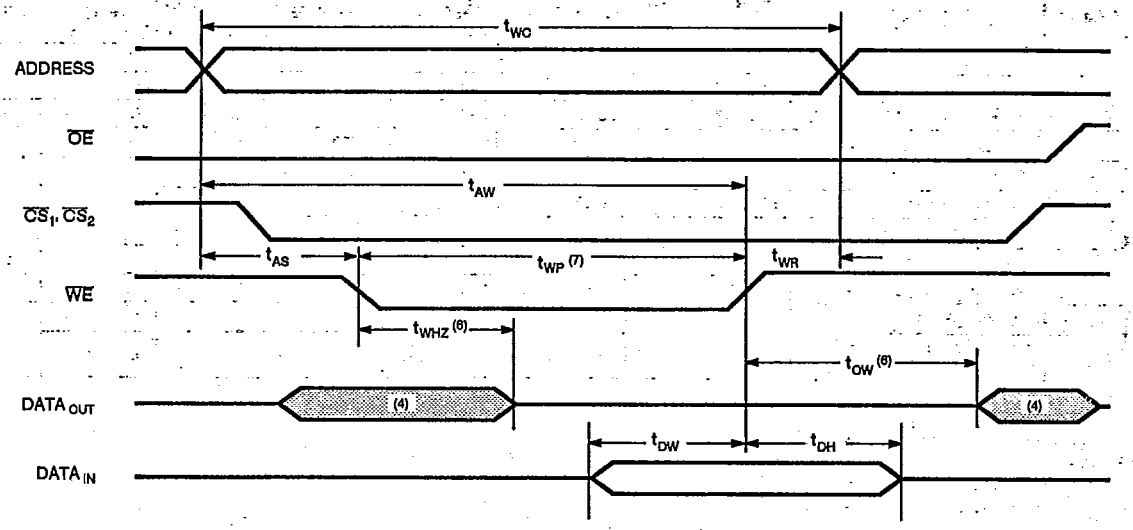
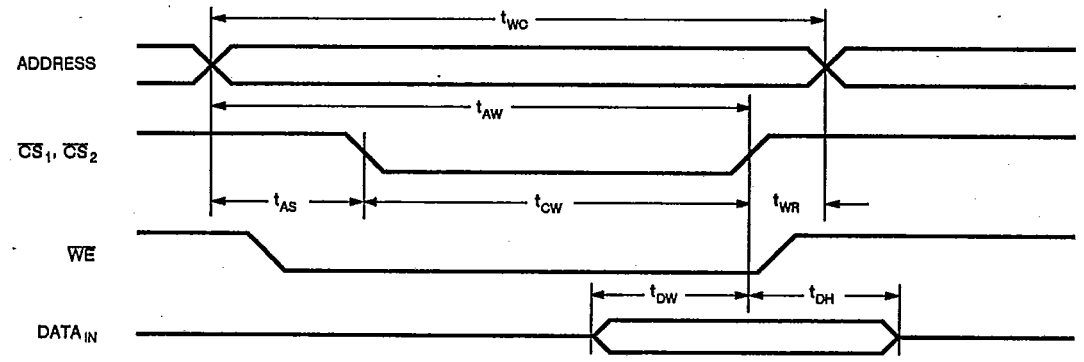
TIMING WAVEFORM OF WRITE CYCLE NO. 1, ($\overline{WE}$ CONTROLLED TIMING)(1, 2, 3, 7)



TIMING WAVEFORM OF WRITE CYCLE NO. 2, ($\overline{CS}$ CONTROLLED TIMING)(1, 2, 3, 5, 8)



NOTES:

1. $\overline{WE}$, $\overline{CS_1}$ or $\overline{CS_2}$ must be high during all address transitions.
2. A write occurs during the overlap (t_{WP}) of a low $\overline{CS_1}$, a low $\overline{CS_2}$ and a low $\overline{WE}$.
3. t_{WR} is measured from the earlier of $\overline{CS_1}$, $\overline{CS_2}$ or $\overline{WE}$ going high to the end of the write cycle.
4. During this period, the I/O pins are in the output state, and input signals must not be applied.
5. If the $\overline{CS}$ low transition occurs simultaneously with or after the $\overline{WE}$ low transition, the outputs remain in the high impedance state.
6. Transition is measured ±200mV from steady state.
7. If $\overline{OE}$ is low during a $\overline{WE}$ controlled write cycle, the write pulse width must be the greater of t_{WP} or (t_{WHZ} + t_{DW}) to allow the I/O drivers to turn off and data to be placed on the bus for the required t_{DW}. If $\overline{OE}$ is high during a $\overline{WE}$ controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified t_{WP}.
8. $\overline{OE}$ = V_{IH}

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TRUTH TABLE

MODE	$\overline{CS_1}$	$\overline{CS_2}$	$\overline{WE}$	$\overline{OE}$	I/O	POWER
Standby	H	X	X	X	High Z	Standby
Standby	X	H	X	X	High Z	Standby
Read	L	L	H	L	D_{OUT}	Active
Write	L	L	L	X	D_{IN}	Active
Read	L	L	H	H	High Z	Active

CAPACITANCE (T_A = +25°C, f = 1.0MHz, V_{CC} = 0V)

SYMBOL	PARAMETER[1]	CONDITIONS	MAX.	UNIT
C_{IN}	Input Capacitance	V_{IN} = 0V	7	pF
C_{OUT}	Output Capacitance	V_{OUT} = 0V	7	pF

NOTE:
1. This parameter is determined by device characterization, but is not production tested.

4

ORDERING INFORMATION

IDT — XXXXX (Device Type) — A (Power) — 999 (Speed) — A (Package) — A (Process/Temperature Range)

Process/Temperature Range:
- Blank — Commercial (0°C to +70°C)
- B — Military (−55°C to +125°C) Compliant to MIL-STD-883, Class B

Package:
- D — Ceramic DIP
- P — Plastic DIP
- C — Sidebraze DIP
- L — Leadless Chip Carrier
- SO — Small Outline IC (Gull Wing)
- Y — Small Outline IC (J-bend)
- E — CERPACK
- F — Flatpack

Speed (Speed in Nanoseconds):
- 15 — Commercial Only
- 19 — Commercial Only
- 20
- 25
- 30
- 35
- 45
- 55 — Military Only
- 70 — Military Only
- 85 — Military Only

Power:
- S — Standard Power
- L — Low Power

Device Type:
- 7198 — 64K (16K x 4-Bit)